

MA6X125

Silicon epitaxial planar type

For switching circuits

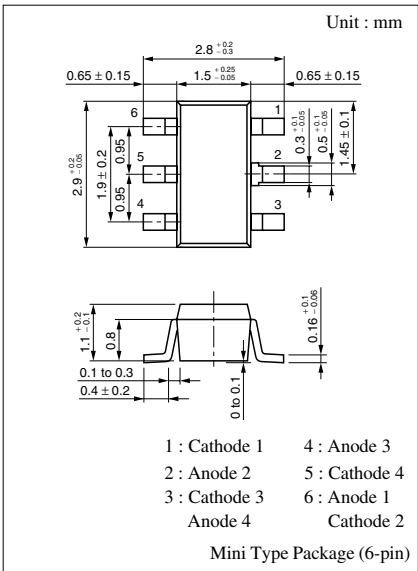
■ Features

- Four-element contained in one package, allowing high-density mounting

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

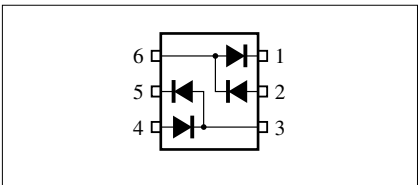
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	40	V
Peak reverse voltage	V_{RM}	40	V
Forward current (DC)*	I_F	100	mA
Peak forward current*	I_{FM}	200	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *1 : Value for single diode



Marking Symbol: M2I

Internal Connection



■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	I_R	$V_R = 40 \text{ V}$			100	nA
Forward voltage (DC)	V_F	$I_F = 100 \text{ mA}$			1.2	V
Reverse voltage (DC)	V_R	$I_R = 100 \mu\text{A}$	40			V
Terminal capacitance	C_t	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			5	pF
Reverse recovery time*3	t_{rr1} *1	$I_F = 10 \text{ mA}, V_R = 6 \text{ V}$		150		ns
	t_{rr2} *2	$I_{rr} = 0.1 \cdot I_R, R_L = 100 \Omega$		90		

Note) 1. Rated input/output frequency: 100 MHz

2. *1 : Between pins 1 and 6, Between pins 3 and 5

*2 : Between pins 2 and 6, Between pins 3 and 4

*3 : t_{rr} measuring circuit

